

UV-B Sensor

GUVB-S11GD



Features

- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- Good Visible Blindness
- High Responsivity & Low Dark Current

Applications

- Pure UV-B Monitoring
- UV Index Monitoring
- Sterilization Lamp Monitoring

Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		3	V	
Forward Current	$I_{f, max.}$		1	mA	
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

Characteristics (at 25°C)

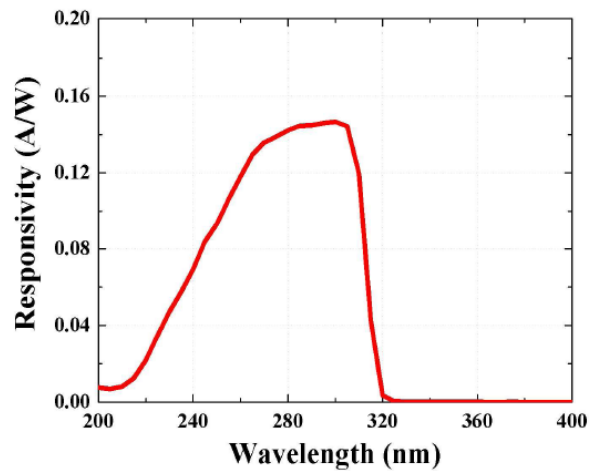
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			1	nA	$V_r = 0.1V$
Photo Current	I_{ph}		1		nA	UVA Lamp, $1mW/cm^2$
Temperature Coefficient	I_{tc}		0.1		%/°C	UVA Lamp
Responsivity	R		0.14		A/W	$\lambda = 350nm,$ $V_r = 0V$
Spectral Detection Range	λ	200		320	nm	
Breakdown Voltage	V_{BR}		5			$I_r = 1\mu A$



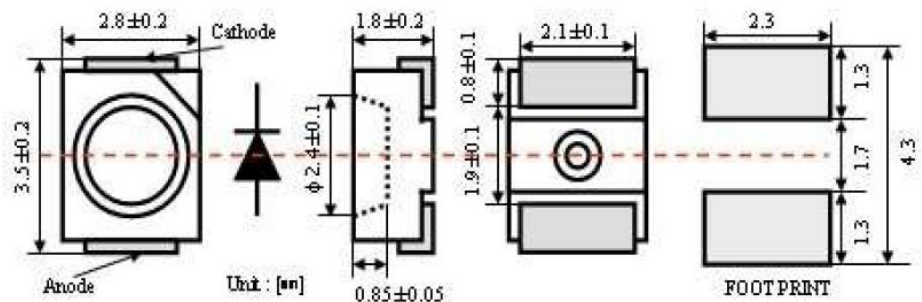
OEC
Opto-Electronic
Components



Responsivity Curve



Outline Diagrams and Dimensions



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